MOSFETs Silicon N-channel MOS (U-MOSⅧ-H)

# **TPH6R30ANL**

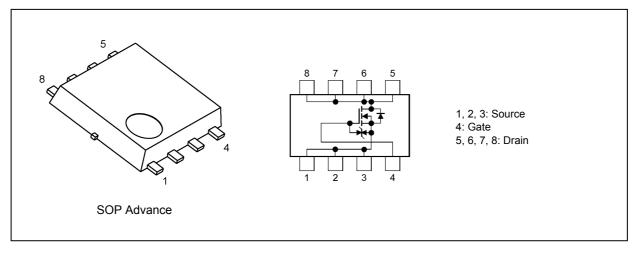
#### 1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators
- Motor Drivers

### 2. Features

- (1) High-speed switching
- (2) Small gate charge :  $Q_{SW} = 14 \text{ nC}$  (typ.)
- (3) Small output charge :  $Q_{oss} = 46 \text{ nC}$  (typ.)
- (4) Low drain-source on-resistance :  $R_{DS(ON)} = 5.1 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- (5) Low leakage current :  $I_{DSS}$  = 10  $\mu$ A (max) ( $V_{DS}$  = 100 V)
- (6) Enhancement mode :  $V_{th}$  = 1.5 to 2.5 V ( $V_{DS}$  = 10 V,  $I_D$  = 0.5 mA)

#### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteris	Symbol	Rating	Unit		
Drain-source voltage			V <sub>DSS</sub>	100	V
Gate-source voltage			V <sub>GSS</sub>	±20	
Drain current (DC)	( T <sub>c</sub> = 25 °C )	(Note 1)	Ι <sub>D</sub>	45	A
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	Ι <sub>D</sub>	66	]
Drain current (pulsed)	(t = 100 µs)	(Note 1)	I <sub>DP</sub>	300	
Power dissipation	( T <sub>c</sub> = 25 °C )		PD	54	W
Power dissipation		(Note 3)	PD	2.5	
Power dissipation		(Note 4)	PD	0.8	
Single-pulse avalanche energy		(Note 5)	E <sub>AS</sub>	63	mJ
Single-pulse avalanche current		(Note 5)	I <sub>AS</sub>	45	A
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal resistance	( T <sub>c</sub> = 25 °C )		R <sub>th(ch-c)</sub>	2.31	°C/W
Channel-to-ambient thermal resistance	( T <sub>a</sub> = 25 °C )	(Note 3)	R <sub>th(ch-a)</sub>	50	
Channel-to-ambient thermal resistance	( T <sub>a</sub> = 25 °C )	(Note 4)	R <sub>th(ch-a)</sub>	156	

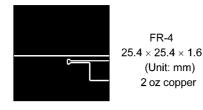
Note 1: Ensure that the channel temperature does not exceed 150 °C.

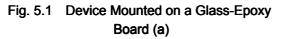
Note 2: Limited by silicon chip capability.

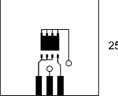
Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V\_DD = 60 V, T\_ch = 25 °C (initial), L = 34  $\mu H, \, I_{AS}$  = 45 A







FR-4 25.4 × 25.4 × 1.6 (Unit: mm) 2 oz copper

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

### 6. Electrical Characteristics

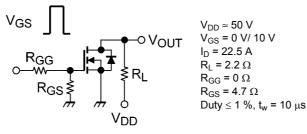
## 6.1. Static Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±16 V, $V_{DS}$ = 0 V	_	_	±10	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V	_	—	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	100	—	_	V
Drain-source breakdown voltage (Note 6)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	65	_	_	
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.5 mA	1.5	—	2.5	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 15 A	_	6.4	10.3	mΩ
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 22.5 A	_	5.1	6.3	

Note 6: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

### 6.2. Dynamic Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 0 V,	_	3300	4300	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	27	56	
Output capacitance	C <sub>oss</sub>		_	410	_	
Gate resistance	r <sub>g</sub>	—		2.1	3.2	Ω
Switching time (rise time)	tr	See Figure 6.2.1	_	7		ns
Switching time (turn-on time)	t <sub>on</sub>		_	18	_	
Switching time (fall time)	t <sub>f</sub>	]		12	_	
Switching time (turn-off time)	t <sub>off</sub>		_	58	_	



#### Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics ( $T_a = 25$ °C unless otherwise specified)

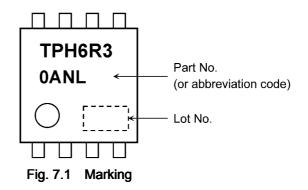
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 50 \text{ V}, \text{ V}_{GS}$ = 10 V, I <sub>D</sub> = 22.5 A	_	55	—	nC
		$V_{DD} \approx 50 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V},$ I_D = 22.5 A	_	27	—	
Gate-source charge 1	Q <sub>gs1</sub>	$V_{DD} \approx 50 \text{ V}, \text{ V}_{GS}$ = 10 V,	_	16	—	
Gate-drain charge	Q <sub>gd</sub>	I <sub>D</sub> = 22.5 A	_	7	_	
Gate switch charge	Q <sub>SW</sub>		_	14	_	
Output charge	Q <sub>oss</sub>	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 0 V, f = 1 MHz		46	_	

## 6.4. Source-Drain Characteristics ( $T_a = 25$ °C unless otherwise specified)

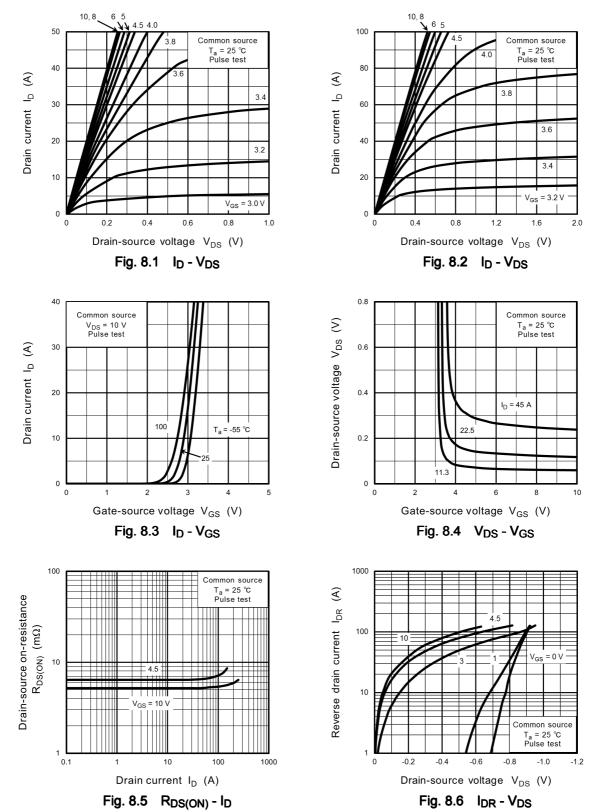
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (1	Note 7)	I <sub>DRP</sub>	(t = 100 μs)	_	—	300	А
Diode forward voltage		V <sub>DSF</sub>	I <sub>DR</sub> = 45 A, V <sub>GS</sub> = 0 V	_	_	-1.2	V
Reverse recovery time			V <sub>R</sub> = 50 V, I <sub>DR</sub> = 11.3 A, V <sub>GS</sub> =	_	48	_	ns
Reverse recovery charge		Q <sub>rr</sub>	0 V, -dI <sub>DR</sub> /dt = 100 A/μs		61		nC

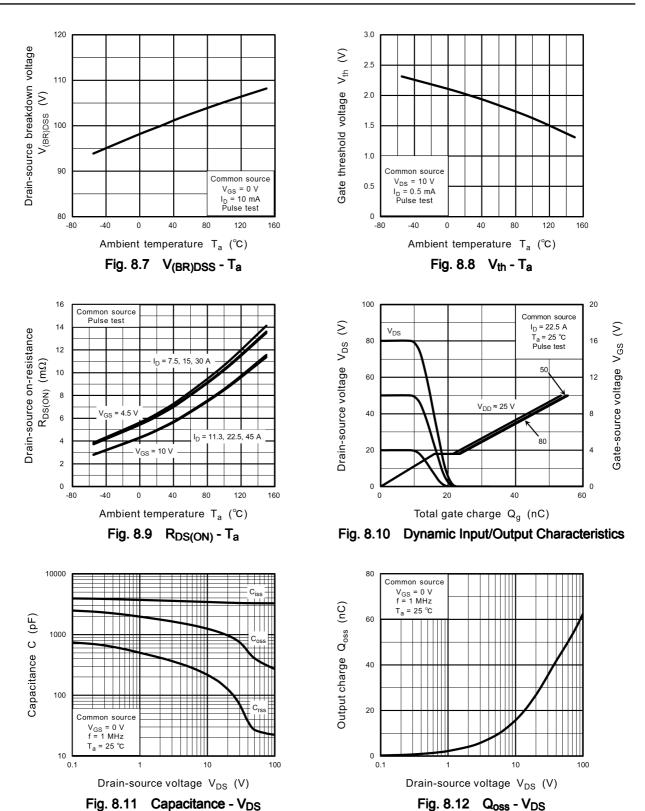
Note 7: Ensure that the channel temperature does not exceed 150 °C.

#### 7. Marking

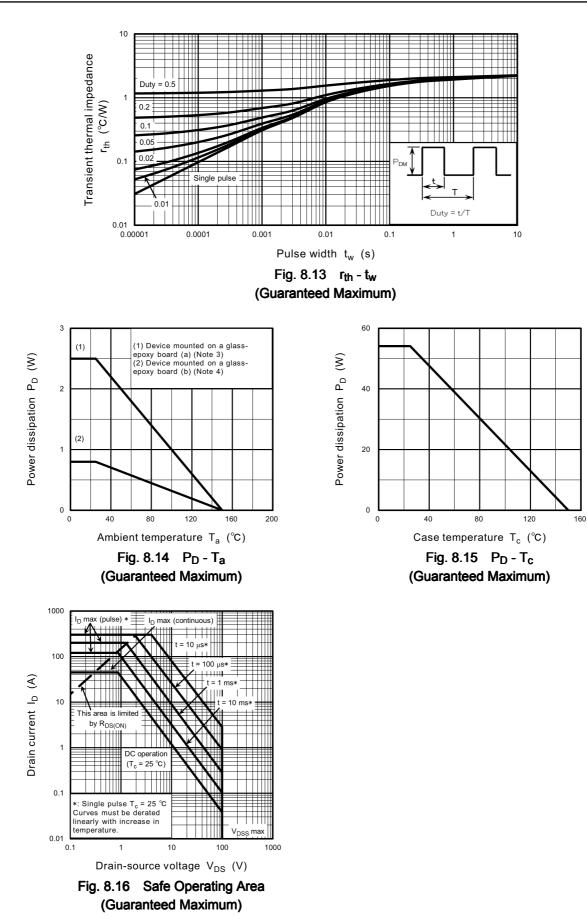


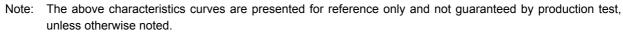
### 8. Characteristics Curves (Note)





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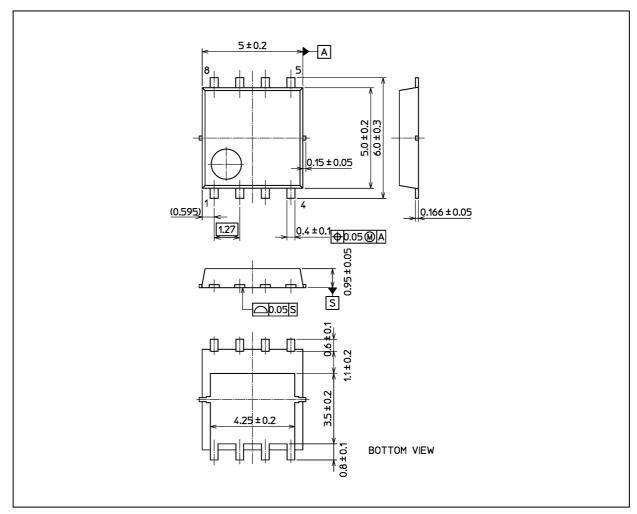




# TPH6R30ANL

#### **Package Dimensions**

Unit: mm



Weight: 0.079 g (typ.)

TOSHIBA: 2-5Q1S

Nickname: SOP Advance

Package Name(s)

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